AMENDMENTS TO THE CLAIMS

1. (withdrawn): A method for manufacturing a light emitting diode having an adhesive layer and a reflective layer, comprising at least the steps of:
forming an LED stack over a first substrate;
forming a first reaction layer over said LED stack;
forming a reflective layer over a second substrate;
forming a second reaction layer over said reflective layer; and
holding together said first reaction layer and said second reaction layer by means of a transparent adhesive layer.

2. (withdrawn): A method for manufacturing a light emitting diode having an adhesive layer and a reflective layer according to claim 1, wherein said reflective layer is a reflective metal layer.

3. (withdrawn): A method for manufacturing a light emitting diode having an adhesive layer and a reflective layer according to claim 2, wherein said reflective metal layer comprises at least a material selected from the group consisting of In, Sn, Al, Au, Pt, Zn, Ag, Ti, Pb, Pd, Ge, Cu, AuBe, AuGe, Ni, PbSn, AuZn, and the like.

4. (withdrawn): A method for manufacturing a light emitting diode having an adhesive layer and a reflective layer according to claim 1, wherein said reflective layer is a reflective oxide layer.

5. (withdrawn): A method for manufacturing a light emitting diode having an adhesive layer and a reflective layer according to claim 4, wherein said reflective oxide layer comprises at least a material selected from the group consisting of SiNx, SiO_2, Al2O3, TiO2, MgO, and the like.

6. (withdrawn): A method for manufacturing a light emitting diode having an adhesive layer and a reflective layer according to claim 1, wherein said transparent

adhesive layer comprises at least a material selected from the group consisting of polyimide (PI), benzocyclobutene (BCB), perfluorocyclobutane (PFCB), and the like.

7. (withdrawn): A method for manufacturing a light emitting diode having an adhesive layer and a reflective layer according to claim 1, wherein said first reaction layer or said second reaction layer comprises at least a material selected from the group consisting of SiNx, Ti, Cr, and the like.

8. (withdrawn): A method for manufacturing a light emitting diode having an adhesive layer and a reflective layer according to claim 1, wherein forming a reflective layer over a second substrate comprises the steps of forming a semiconductor stack over said second substrate and forming a reflective layer over said semiconductor stack.

9. (withdrawn): A method for manufacturing a light emitting diode having an adhesive layer and a reflective layer according to claim 1, further comprising the step of removing said first substrate.

10. (withdrawn): A method for manufacturing a light emitting diode having an adhesive layer and a reflective layer, comprising at least the steps of:
forming an LED stack over a first substrate;
forming a first reaction layer over said LED stack;
forming a second reaction layer over a reflective metal substrate; and
holding together said first reaction layer and said second reaction layer by means of a transparent adhesive layer.

11. (withdrawn): A method for manufacturing a light emitting diode having an adhesive layer and a reflective layer according to claim 10, wherein said reflective metal substrate comprises at least a material selected from the group consisting of Sn, Al, Au, Pt, Zn, Ag, Ti, Pb, Pd, Ge, Cu, AuBe, AuGe, Ni, PbSn, AuZn, and the like.

12. (withdrawn): A method for manufacturing a light emitting diode having an adhesive layer and a reflective layer according to claim 10, wherein said transparent adhesive layer comprises at least a material selected from the group consisting of polyimide (PI), benzocyclobutene (BCB), perfluorocyclobutane (PFCB), and the like.

13. (withdrawn): A method for manufacturing a light emitting diode having an adhesive layer and a reflective layer according to claim 10, wherein said first reaction layer or said second reaction layer comprises at least a material selected from the group consisting of SiNx, Ti, Cr, and the like.

14. (withdrawn): A method for manufacturing a light emitting diode having an adhesive layer and a reflective layer according to claim 10, wherein the step of forming a second reaction layer over a reflective metal substrate comprises the steps of forming a reflective layer over said reflective metal substrate and forming a second reaction layer over said reflective layer.

15. (withdrawn): A method for manufacturing a light emitting diode having an adhesive layer and a reflective layer according to claim 10, further comprising the step of removing said first substrate.

16. (withdrawn): A method for manufacturing a light emitting diode having an adhesive layer and a reflective layer, comprising at least the steps of:

forming an LED stack over a first substrate;

forming a reflective layer over said LED stack;

forming a first reaction layer over said reflective layer;

forming a second reaction layer over a second substrate; and

holding together said first reaction layer and said second reaction layer by means of an adhesive layer.

17. (withdrawn): A method for manufacturing a light emitting diode having an adhesive layer and a reflective layer according to claim 16, wherein said reflective layer is a reflective metal layer.

18. (withdrawn): A method for manufacturing a light emitting diode having an adhesive layer and a reflective layer according to claim 16, wherein said reflective layer is a reflective oxide layer.

19. (withdrawn): A method for manufacturing a light emitting diode having an adhesive layer and a reflective layer according to claim 17, wherein said reflective metal layer comprises at least a material selected from the group consisting of In, Sn, Al, Au, Pt, Zn, Ag, Ti, Pb, Pd, Ge, Cu, AuBe, AuGe, Ni, PbSn, AuZn, and the like.

20. (withdrawn): A method for manufacturing a light emitting diode having an adhesive layer and a reflective layer according to claim 18, wherein said reflective oxide layer comprises at least a material selected from the group consisting of SiNx, SiO_2, Al2O3, TiO2, MgO, and the like.

21. (withdrawn): A method for manufacturing a light emitting diode having an adhesive layer and a reflective layer according to claim 16, wherein said first reaction layer or said second reaction layer comprises at least a material selected from the group consisting of SiNx, Ti, Cr, and the like.

22. (withdrawn): A method for manufacturing a light emitting diode having an adhesive layer and a reflective layer according to claim 16, further comprising the step of removing said first substrate.

23. (currently amended): A light emitting diode having an adhesive layer and a reflective layer, comprising at least:
a substrate;

a reflective layer formed over the substrate;

a first reaction layer formed over said reflective layer;

a transparent adhesive layer formed over said first reaction layer;

a second reaction layer formed over said transparent adhesive layer;

and an LED stack formed over said second reaction layer.

24. (original): A light emitting diode having an adhesive layer and a reflective layer according to claim 23, further comprising a transparent conductive layer between said second reaction layer and said LED stack.

25. (original): A light emitting diode having an adhesive layer and a reflective layer according to claim 23, wherein said reflective layer is a reflective metal layer.

26. (original): A light emitting diode having an adhesive layer and a reflective layer according to claim 23, wherein said reflective layer is a reflective oxide layer.

27. (currently amended): A light emitting diode having an adhesive layer and a reflective layer according to claim 25, wherein said reflective metal layer comprises at least a material selected from the group consisting of In, Sn, Al, Au, Pt, Zn, Ag, Ti, Pb, Pd, Ge, Cu, AuBe, AuGe, Ni, PbSn, and AuZn~~, and the like~~.

28. (currently amended): A light emitting diode having an adhesive layer and a reflective layer according to claim 26, wherein said reflective oxide layer comprises at least a material selected from the group consisting of SiNx, SiO_2, Al2O3, TiO2, and MgO~~, and the like~~.

29. (currently amended): A light emitting diode having an adhesive layer and a reflective layer according to claim 23, wherein said transparent adhesive layer comprises at least a material selected from the group consisting of polyimide (PI), benzocyclobutene (BCB), and perfluorocyclobutane (PFCB)~~, and the like~~.

30. (currently amended): A light emitting diode having an adhesive layer and a reflective layer according to claim 23, wherein said first reaction layer or said second reaction layer comprises at least a material selected from the group consisting of SiNx, Ti, and Cr~~, and the like~~.

31. (withdrawn): A light emitting diode having an adhesive layer and a reflective layer, comprising at least:
a substrate;
a first reaction layer formed over the substrate;
a adhesive layer formed over said first reaction layer;
a second reaction layer formed over said adhesive layer;
a reflective layer formed over said second reaction layer; and
an LED stack formed over said reflective layer.

32. (withdrawn): A light emitting diode having an adhesive layer and a reflective layer according to claim 31, further comprising a transparent conductive layer between said reflective layer and said LED stack.

33. (withdrawn): A light emitting diode having an adhesive layer and a reflective layer according to claim 31, wherein said reflective layer is a reflective metal layer.

34. (withdrawn): A light emitting diode having an adhesive layer and a reflective layer according to claim 31, wherein said reflective layer is a reflective oxide layer.

35. (withdrawn): A light emitting diode having an adhesive layer and a reflective layer according to claim 33, wherein said reflective metal layer comprises at least a material selected from the group consisting of In, Sn, Al, Au, Pt, Zn, Ag, Ti, Pb, Pd, Ge, Cu, AuBe, AuGe, Ni, PbSn, AuZn, and the like.

36. (withdrawn): A light emitting diode having an adhesive layer and a reflective layer according to claim 34, wherein said reflective oxide layer comprises at least a

material selected from the group consisting of SiNx, SiO_2, Al2O3, TiO2, MgO, and the like.

37. (withdrawn): A light emitting diode having an adhesive layer and a reflective layer according to claim 31, wherein said transparent adhesive layer comprises at least a material selected from the group consisting of polyimide (PI), benzocyclobutene (BCB), perfluorocyclobutane (PFCB), and the like.

38. (withdrawn): A light emitting diode having an adhesive layer and a reflective layer according to claim 31, wherein said first reaction layer or said second reaction layer comprises at least a material selected from the group consisting of SiNx, Ti, Cr, and the like.

39. (currently amended): A light emitting diode having an adhesive layer and a reflective layer, comprising at least:
a reflective metal substrate;
a first reaction layer formed over the reflective metal substrate;
a transparent adhesive layer formed over said first reaction layer;
a second reaction layer formed over said transparent adhesive layer;
and an LED stack formed over said second reaction layer.

40. (original): A light emitting diode having an adhesive layer and a reflective layer according to claim 39, further comprising a transparent conductive layer between said second reaction layer and said LED stack.

41. (currently amended): A light emitting diode having an adhesive layer and a reflective layer according to claim 39, wherein said reflective metal substrate comprises at least a material selected from the group consisting of Sn, Al, Au, Pt, Zn, Ag, Ti, Pb, Pd, Ge, Cu, AuBe, AuGe, Ni, PbSn, and AuZn~~, and the like~~.

42. (currently amended): A light emitting diode having an adhesive layer and a

reflective layer according to claim 39, wherein said transparent adhesive layer comprises at least a material selected from the group consisting of polyimide (PI), benzocyclobutene (BCB), and perfluorocyclobutane (PFCB)~~, and the like~~.

43. (currently amended): A light emitting diode having an adhesive layer and a reflective layer according to claim 39, wherein said first reaction layer or said second reaction layer comprises at least a material selected from the group consisting of SiNx, Ti, and Cr~~, and the like~~.

44. (new): A light emitting diode having an adhesive layer and a reflective layer, comprising at least:

a reflective means;

a first reaction layer formed over said reflective means;

a transparent adhesive layer formed over said first reaction layer;

a second reaction layer formed over said transparent adhesive layer; and

an LED stack formed over said second reaction layer.